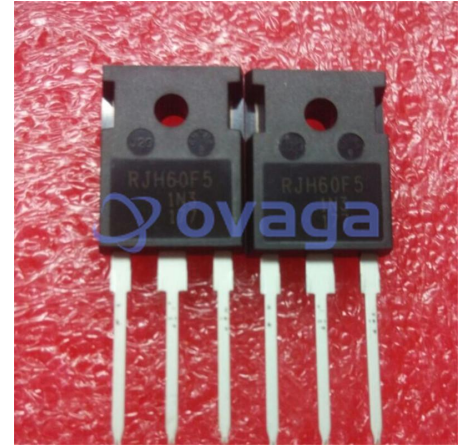


Silicon N Channel IGBT High Speed Power Switching

Manufacturers	Renesas Technology Corp
Package/Case	TO-247
Product Type	Transistors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for RJH60F5DPQ or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

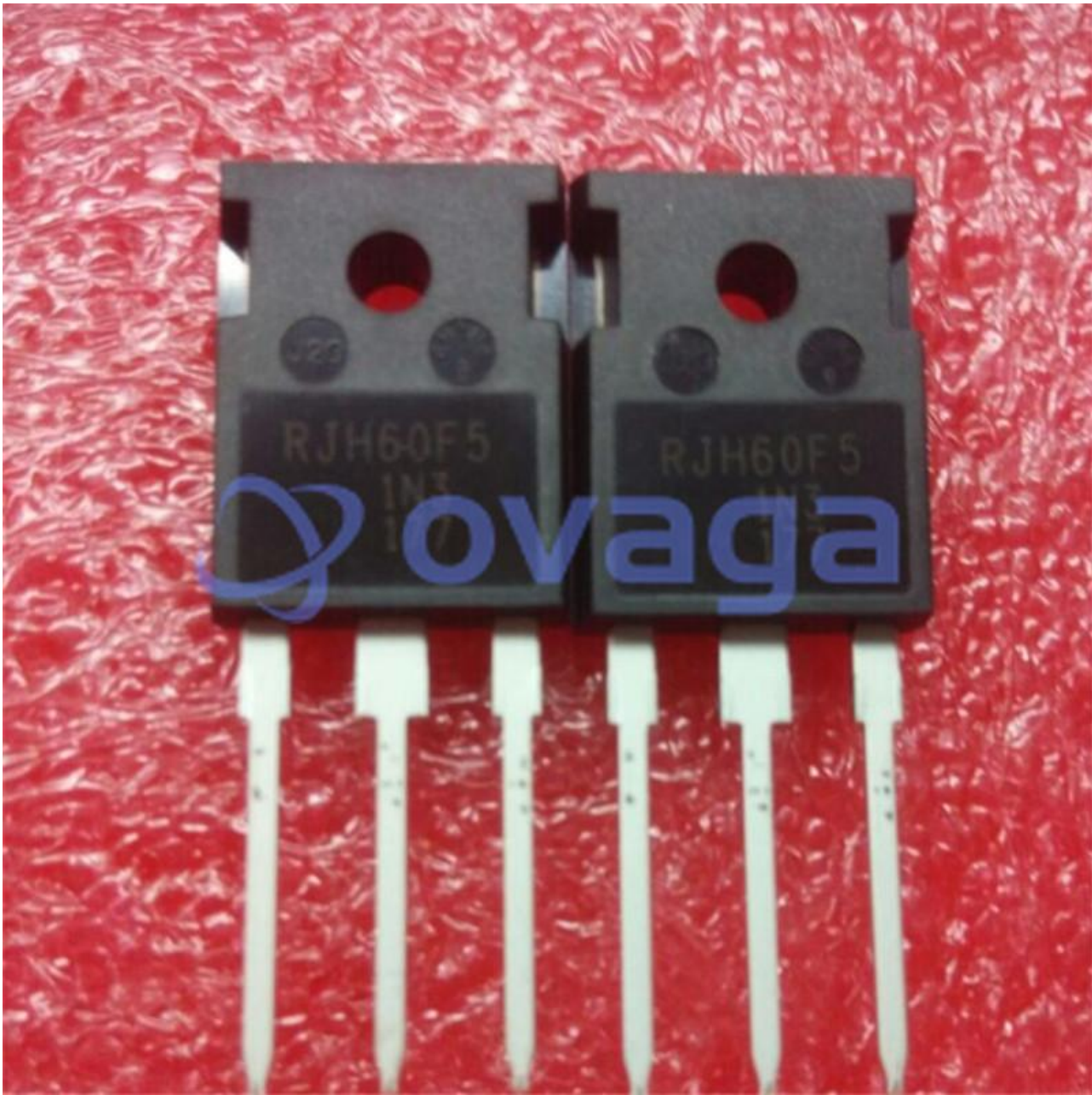
RJH60F5DPQ is a power MOSFET transistor manufactured by Renesas Electronics. It is designed for use in high-power switching applications such as power supplies, motor control, and inverters.

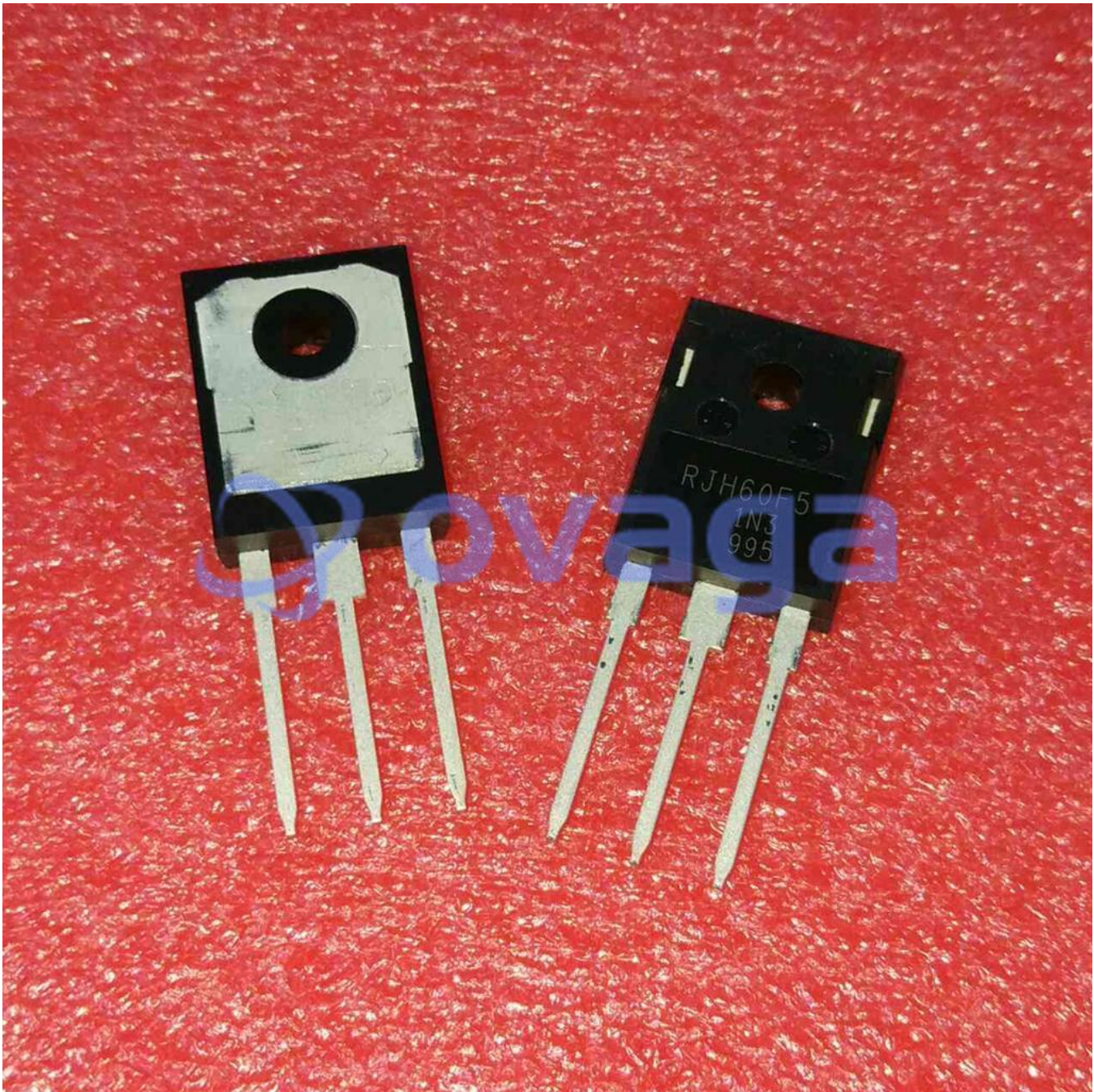
Features

- Drain-Source voltage (VDS) rating of 600V
- Continuous Drain Current (ID) rating of 60A
- Low on-state resistance (RDS(on)) of 0.085 ohms
- Fast switching speed
- Low gate charge

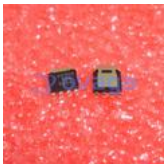
Application

- AC and DC motor control
- Switch-mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)
- Inverters for solar power generation and electric vehicles
- Industrial equipment and automation systems





Related Products



[RJK0305DPB-02#J0](#)

Renesas Technology Corp
TO252-4



[RJK0332DPB](#)

Renesas Technology Corp
LFPAK



[RJH60F5DPQ-A0#T0](#)

Renesas Technology Corp
TO-247A



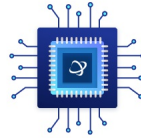
[RJK0330DPB](#)

Renesas Technology Corp
LFPAK



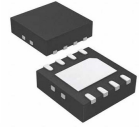
[RJK0353DPA](#)

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QFN8 56/WPAK



[RJK0305DPB-00#J0](#)

Renesas Technology Corp
LFPAK-5



[RJK0365DPA-00#J0](#)

Renesas Technology Corp
QFN-8



[RJK1054DPB-00#J5](#)

Renesas Technology Corp
SC-100